

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1 1 - 24. (Cancelled)

1 25. (Previously Presented) A method of manufacturing an integrated circuit
2 comprising:
3 forming trenches in a substrate comprising a germanium-containing layer;
4 providing a strained semiconductor material above the germanium-containing
5 layer and on sidewalls of the trenches; and
6 providing insulative material in the apertures to form trench isolation regions.

1 26. (Previously Presented) The method of claim 25, wherein the strained
2 semiconductor material is formed on sidewalls of the trenches.

1 27. (Previously Presented) The method of claim 25, further comprising siliciding the
2 strained semiconductor material.

1 28. (Previously Presented) The method of claim 25, wherein the germanium-
2 containing layer comprises a silicon-germanium material.

1 29. (Previously Presented) The method of claim 25, wherein the strained
2 semiconductor material comprises strained silicon.

1 30. (Previously Presented) The method of claim 25, wherein the insulative material
2 comprises silicon dioxide.

1 31. (Previously Presented) The method of claim 25, wherein the first layer is above a
2 buried oxide layer.

1 32. (Previously Presented) The method of claim 31, wherein the trenches extend
2 through the germanium-containing layer to the buried oxide layer.

1 33. (Previously Presented) A method of producing an integrated circuit comprising:
2 forming a trench having sidewalls in a substrate comprising a silicon-germanium
3 layer;
4 forming a strained silicon material above the silicon-germanium layer and on the
5 sidewalls of the trench; and
6 filling the trench with an insulative material to form a trench isolation region.

1 34. (Previously Presented) The method of claim 33, wherein the strained silicon
2 material is formed on sidewalls of the trenches.

1 35. (Previously Presented) The method of claim 33, further comprising siliciding the
2 strained silicon material.

1 36. (Previously Presented) The method of claim 33, wherein the trench extends
2 through the silicon-germanium layer to an underlying buried oxide layer.